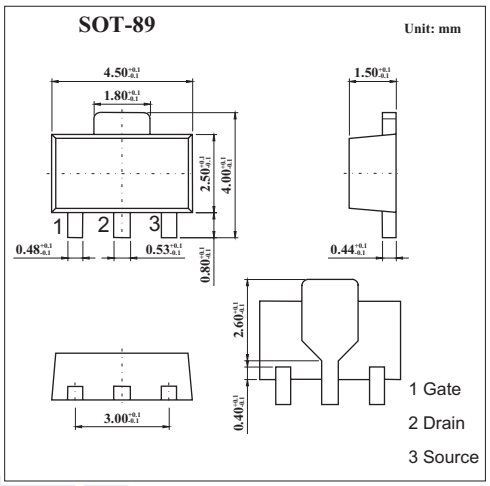
P-Channel MOS Silicon FET

2SJ288



Features

- Low on resistance
- Very high-speed switching
- Low-voltage drive

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage VGS=0	VDSS	-60	V
Gate to source voltage VDS=0	VGSS	±15	V
Drain current (DC)	ID	-500	m A
Drain current(pulse) *	ID	-2	A
Power dissipation	PD	3.5	W
Channel temperature	Tch	150	℃
Storage temperature	Tstg	-55 to +150	℃

* PW ⩽ 10 μs; d ⩽ 1%.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	IDSS	VDS=-60V,VGS=0			-100	μA
Gate leakage current	IGSS	VGS=±12V,VDS=0			±10	μA
Gate cut-off voltage	VGS(off)	VDS=-10V,ID=-1mA	-1.0		-2.0	V
Forward transfer admittance	|Yfs|	VDS=-10V,ID=-250mA	240	400		ms
Drain to source on-state resistance	RDS(on)	VGS=-10V,ID=-250mA		2.2	3.0	Ω
		VGS=-4V,ID=-250mA		3.0	4.0	Ω
Input capacitance	Ciss	VDS=-20V,VGS=0,f=1MHZ		45		pF
Output capacitance	Coss			20		pF
Reverse transfer capacitance	Crss			5		pF
Turn-on delay time	td(on)	VDD=-30V,ID=--250mA RL=120Ω		7		ns
Rise time	tr			10		ns
Turn-off delay time	td(off)			35		ns
Fall time	tf			20		ns

Marking

Marking	JE